Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

forming a protrusion on a semiconductor substrate having a first area and a second area surrounding the first area, the protrusion protruding above the first area;

disposing a support on a surface of the semiconductor substrate on which the protrusion is formed, ~~of the semiconductor substrate ,~~ a part of the support overlapping with the second area being thicker than another part of the support overlapping with the first area; and

grinding the semiconductor substrate from a surface opposite to the surface on which the protrusion is formed.

2. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

disposing a resin layer on a first area of a semiconductor substrate, the semiconductor substrate having a second area surrounding the first area;

disposing a support on a surface of the semiconductor substrate on which the resin layer is disposed, ~~of the semiconductor substrate ,~~ a part of the support overlapping with the second area being thicker than another part of the support overlapping with the first area; and

grinding the semiconductor substrate from a surface opposite- to the surface on which the resin layer is disposed.

3. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

disposing a resin layer on a first area of a semiconductor substrate, the semiconductor substrate having a second area surrounding the first area;

disposing a protruding electrode on the resin layer;

disposing a support on a surface of the semiconductor substrate on which the resin layer is disposed, ~~of the semiconductor substrate ,~~ a part of the support overlapping with the second area being thicker than another part of the support overlapping with the first area; and

grinding the semiconductor substrate from a surface opposite to the surface on which the resin layer is disposed.

4. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any one of Claims 1 through 3, wherein:~~Claim 1,

——————the second area ~~is~~ being an outer end of the semiconductor substrate.

5. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any one of Claims 1 through 4, wherein:~~Claim 1,

——————the step of disposing the support ~~includes a step of~~including forming the support by coating the semiconductor substrate with resin by spin-coating.

6. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 5, ~~wherein:~~

——————the step of disposing the support ~~includes a step of~~including forming a raised portion of the resin on the second area.

7. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 5, ~~or 6, wherein:~~

——————the step of disposing the support ~~includes a step of~~including pressing to planarize a surface of the resin.

8. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein:~~

~~———————~~the support ~~includes~~ including an adhesive sheet having an adhesive layer thicker than the height of the protrusion; and

the step of disposing the support ~~includes a e step of~~including forming the support by pressing the semiconductor substrate against the adhesive sheet to eject at least a part of the adhesive layer outside the protrusion.

9. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 2, ~~wherein:~~

~~———————~~the support ~~includes~~ including an adhesive sheet having an adhesive layer thicker than the thickness of the resin layer; and

the step of disposing the support ~~includes a step of~~further including forming the support by pressing the semiconductor substrate against the adhesive sheet to eject at least a part of the adhesive layer outside the resin layer.

10. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 3, ~~wherein:~~

~~———————~~the support ~~includes~~ including an adhesive sheet having an adhesive layer thicker than the total thickness of the resin layer and the protruding electrode; and

the step of disposing the support ~~includes a step of~~including forming the support by pressing the semiconductor substrate against the adhesive sheet to eject at least a part of the adhesive layer outside the resin layer and the protruding electrode.

11. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

forming a protrusion on a semiconductor substrate having a first area and a second area surrounding the first area, the protrusion protruding above the first area;

disposing a support on a surface of the semiconductor substrate on which the protrusion is formed, ~~of the semiconductor substrate~~ so that a through hole of the support overlaps with the first area; and

grinding the semiconductor substrate from a surface opposite to the surface on which the protrusion is formed.

12. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

disposing a resin layer on a first area of a semiconductor substrate, the semiconductor substrate having a second area surrounding the first area;

disposing a support on a surface of the semiconductor substrate on which the resin layer is disposed, ~~of the semiconductor substrate~~ so that a through hole of the support overlaps with the first area; and

grinding the semiconductor substrate from a surface opposite to the surface on which the resin layer is disposed.

13. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

disposing a resin layer on a first area of a semiconductor substrate, the semiconductor substrate having a second area surrounding the first area;

disposing a protruding electrode on the resin layer;

disposing a support on a surface of the semiconductor substrate on which the resin layer is disposed, ~~of the semiconductor substrate~~ so that a through hole of the support overlaps with the first area; and

grinding the semiconductor substrate from a surface opposite to the surface on which the resin layer is disposed.

14. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any one of Claims 11 through 13, wherein:~~Claim 11,

——————the second area ~~is~~ being an outer end of the semiconductor substrate.

15. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 14, ~~wherein:~~

——————the support ~~is~~ being formed on the periphery of the through hole and has a step ~~for disposing the~~that disposes an outer end of the semiconductor substrate.

16. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any one of Claims 11 through 15, wherein:~~Claim 11,

——————the support ~~is~~ being made of resin.

17. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 16, ~~wherein:~~

——————the step of disposing the support ~~includes a step of~~including curing the resin.

18. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any one of Claims 1 through 17, wherein:~~Claim 1,

——————the first area ~~is~~ being an area of an effective chip having an integrated circuit and becoming a product; and

the second area ~~is~~ being an area of a periphery chip which does not become a product.

19. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any one of Claims 1 through 18,~~Claim 1, further comprising: ~~the step of:~~

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

20. (Currently Amended) The method of manufacturing a semiconductor device according to ~~any of Claims 1 through 19~~Claim 1, further comprising: ~~the step of:~~

removing the support from the semiconductor substrate after the step of grinding the semiconductor substrate.

21. (Currently Amended) A method of manufacturing a semiconductor device, comprising: ~~the steps of:~~

disposing a resin layer on a first and a second areas of a semiconductor substrate, the first area becoming a product and the second area surrounding the first area not becoming a product;

disposing a protruding electrode on the resin layer and above the first and the second areas; and

grinding the semiconductor substrate from a surface opposite to the surface on which the resin layer is disposed.

22. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 21, ~~wherein:~~

~~——————~~the second area ~~includes~~ including an area of a part which includes a side face of the semiconductor substrate and becomes a semiconductor chip.

23. (Currently Amended) A semiconductor device manufactured by the method according to ~~any one of Claims 1 through 22~~Claim 1.

24. (Original) A circuit board equipped with the semiconductor device according to Claim 23.

25. (Original) An electronic apparatus comprising the semiconductor device according to Claim 23.

26. (New) The method of manufacturing a semiconductor device according to Claim 2, the second area being an outer end of the semiconductor substrate.

27. (New) The method of manufacturing a semiconductor device according to Claim 3, the second area being an outer end of the semiconductor substrate.

28. (New) The method of manufacturing a semiconductor device according to Claim 2, the step of disposing the support including forming the support by coating the semiconductor substrate with resin by spin-coating.

29. (New) The method of manufacturing a semiconductor device according to Claim 3, the step of disposing the support including forming the support by coating the semiconductor substrate with resin by spin-coating.

30. (New) The method of manufacturing a semiconductor device according to Claim 28, the step of disposing the support including forming a raised portion of the resin on the second area.

31. (New) The method of manufacturing a semiconductor device according to Claim 29, the step of disposing the support including forming a raised portion of the resin on the second area.

32. (New) The method of manufacturing a semiconductor device according to Claim 28, the step of disposing the support including pressing to planarize a surface of the resin.

33. (New) The method of manufacturing a semiconductor device according to Claim 29, the step of disposing the support including pressing to planarize a surface of the resin.

34. (New) The method of manufacturing a semiconductor device according to Claim 2, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

35. (New) The method of manufacturing a semiconductor device according to Claim 3, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

36. (New) The method of manufacturing a semiconductor device according to Claim 2, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

37. (New) The method of manufacturing a semiconductor device according to Claim 3, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

38. (New) The method of manufacturing a semiconductor device according to Claim 11, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

39. (New) The method of manufacturing a semiconductor device according to Claim 11, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

40. (New) The method of manufacturing a semiconductor device according to Claim 12, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

41. (New) The method of manufacturing a semiconductor device according to Claim 12, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

42. (New) The method of manufacturing a semiconductor device according to Claim 13, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

43. (New) The method of manufacturing a semiconductor device according to Claim 13, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

44. (New) The method of manufacturing a semiconductor device according to Claim 12, the support being made of resin.

45. (New) The method of manufacturing a semiconductor device according to Claim 44, the step of disposing the support including curing the resin.

46. (New) The method of manufacturing a semiconductor device according to Claim 13, the support being made of resin.

47. (New) The method of manufacturing a semiconductor device according to Claim 46, the step of disposing the support including curing the resin.

48. (New) The method of manufacturing a semiconductor device according to Claim 2, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

49. (New) The method of manufacturing a semiconductor device according to Claim 3, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

50. (New) The method of manufacturing a semiconductor device according to Claim 11, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

51. (New) The method of manufacturing a semiconductor device according to Claim 12, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

52. (New) The method of manufacturing a semiconductor device according to Claim 13, the first area being an area of an effective chip having an integrated circuit and becoming a product; and

the second area being an area of a periphery chip which does not become a product.

53. (New) The method of manufacturing a semiconductor device according to Claim 2, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

54. (New) The method of manufacturing a semiconductor device according to Claim 3, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

55. (New) The method of manufacturing a semiconductor device according to Claim 11, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

56. (New) The method of manufacturing a semiconductor device according to Claim 12, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.

57. (New) The method of manufacturing a semiconductor device according to Claim 13, further comprising:

cutting the semiconductor substrate with the support disposed on the semiconductor substrate after the step of grinding the semiconductor substrate.